

SPiDeR (Silicon Pixel Detector Research) at EUDET Telescope







- Sensor overview with lab results
 - TPAC - FORTIS

• Beam test 09





D. Cussans on behalf of J.J. Velthuis, A. Caldarone for the SPIDER collaboration









TPAC is the sensor aimed at digital calorimetry

Tests with Fe55 and beam test

FORTIS aimed at tracking Tests with light, Fe55 and beam tests

Cherwell: The future

TPAC: Digital Calorimetry



- Average number of charged particles in EM shower ∝ incident energy
 - Fluctuations due to statistical nature of shower
- Average energy in sensitive layers ∝ number of charged particles
 - Fluctuations due to angle of incidence, velocity and Landau spread
- Hence, number of charged particles is an intrinsically better measure than the energy deposited
 - Clearest with ideal calorimeter; no experimental effects
 - Energy deposited ("analogue"

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Digital Calorimetry: Concept



• Can we measure the number of charged particles?

- Possible to get close to the analogue ideal resolution with low noise electronics
- Can we get anywhere near the ideal resolution for the digital case?
 - Make pixellated detector with small pixels
 - Probability of more than one charged particle per pixel can be made small
 - Allows binary readout = hit/no hit
- EM shower density ~100/mm² in core
 - Need pixels ~ 50µm
 - Results in huge number of pixels in a real ECAL $\sim 10^{12}$ pixels



TPAC Pixel



- Gain 136uV/e
- Noise 23e-

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- Power 8.9uW
- 150ns "hit" pulse
 wired to row
 logic
- Shaped pulses return to baseline

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NW DPW

- 50um pixel
- 4 diodes
- 160 transistors
- 27 unit capacitors
- 1 resistor (4Mohm)
- Configuration SRAM
 - Per Pixel Mask
 - Comparator trim (6 bits)

SPiDeR

FEE Workshop 2009

Monday, 19 October 2009

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TPAC Fe55





- Primary 55Fe peak gives calibrated gain of $128\mu V/e-$
- Width of 55Fe peak gives noise of 27e-
- See Kα and Kβ clearly separated



TPAC beam test

- TPAC in beam tests
 - 120 GeV π & 20-120 GeV e^-
 - 6 TPAC sensors (layers) in stack
 - 170k pixels in total
 - 1cm x 1cm active area
 - Three scintillators/PMTs installed
 - Used to tag time of particles within bunch trains
 - Data seems good
 - Scintillators/PMTs give good time tags for particles
 - Events were seen in all layers



USB-based DAQ setup on H6B beam line at CERN







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- FORTIS is the first 4T MAPS for Particle Physics
 3T CMOS
 - Simple architecture
 - Readout and charge collection area are the same
 - 4T CMOS
 - Three additional elements
 - Readout and charge collection area are at different points





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VRESET

4T Pixel Advantages

- Low Noise \mathbf{O}
 - readout node separated from charge collection area
 - The reset noise and fixed pattern noise (FPN) can be removed by in-pixel correlated double sampling (CDS)
- **High Conversion Gain** •
 - Charge is collected on large diode then transferred to the floating diffusion
 - Large C gives fast and complete charge collection
 - Small C yields large gain







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Deep Pwell



• Problem in MAPS:

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- PMOS electronics need Nwell
- Nwell acts as charge collection diode
- So can't make PMOS without losing huge amount of Q
- New development: make deep pwell with Nwell inside → can do CMOS
 - Road to data processing in pixel







Substrate Resistivity



- High resistivity (intrinsic) silicon enlarges the depletion region to fully occupy the pixel
 - Majority of deposited charge now falls in a depletion region and is collected by electric field
 - Improved charge collection efficiency
 - Faster charge collection (drift vs diffusion)
- Some FORTIS have high res



















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• ⁵⁵Fe Photons (preliminary)

- Conversion gain = 56 μ V/e⁻

- Noise (from dark fwhm) = $7.7e^{-1}$





Some test beam pictures







Some test beam pictures







Some test beam pictures





We see hits...







We see hits...









Raw signals







Raw S/N for each pixel





Pixel Noise

SPiDeR





Cluster signal



 Corresponds to S/N~50

SPiD

 Data analysis just started
 Still need to match up with telescope













BRISTOL The future: Cherwell





- 100% fill factor with integrated sensor and readout electronics

- Incorporation of complex logic within a pixel
- Investigation of data reduction/clustering
- Low noise using transfer gate, CDS and in-pixel amplification









Future plans

- Complete beam test analysis for FORTIS and TPAC
- Test all FORTIS and TPAC variants in the lab
- Test results will drive DECAL and CHERWELL architectures
- Perform beam test at DESY with TPAC
- Waiting for next April fools day...